

### FEATURES

· BROAD BAND INTERNALLY MATCHED FET

· HIGH POWER

P1dB= 36.5dBm at 5.85GHz to 6.75GHz

· HIGH GAIN

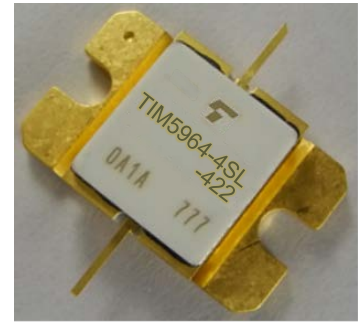
G1dB= 8.0dB(Min.) at 5.85GHz to 6.75GHz

· HERMETICALLY SEALED PACKAGE

· LOW INTERMODULATION DISTORTION

IM3= -45dBc at Pout= 25.5dBm

Single Carrier Level.



### RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 1.1A f = 5.85 to 6.75GHz	dBm	35.5	36.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	—	—
Drain Current	IDS1		A	—	1.1	1.3
Gain Flatness	ΔG		dB	—	—	±0.6
Power Added Efficiency	ηadd		%	—	35	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 25.5dBm, Δf= 5MHz (Single Carrier Level)	dBc	-42	-45	—
Drain Current	IDS2		A	—	1.1	1.3
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin - P1dB) X Rth(c-c)	°C	—	—	80

**Recommended Gate Resistance(Rg): 150 Ω**

### ELECTRICAL CHARACTERISTICS ( Ta= 25°C )

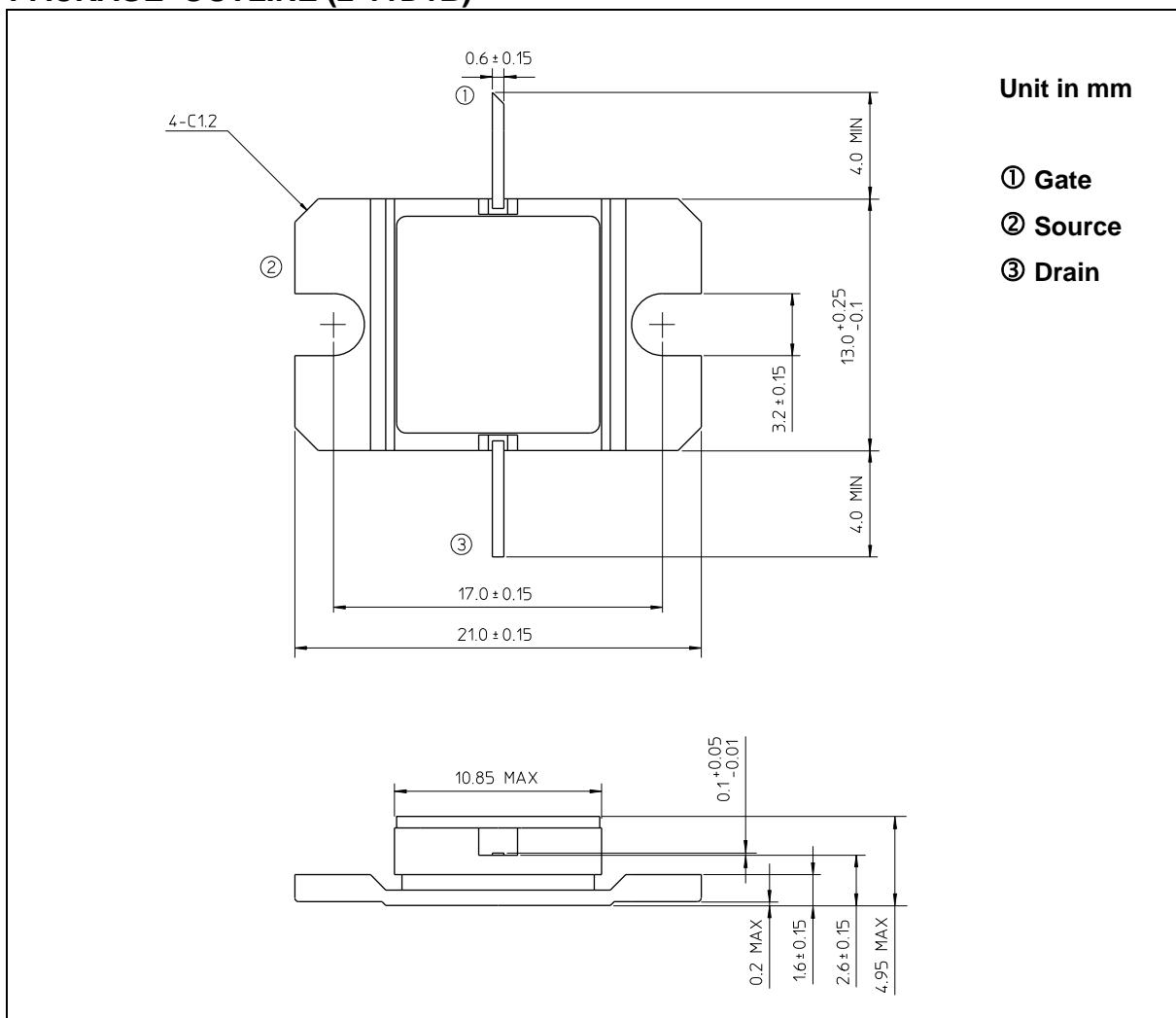
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 1.5A	S	—	0.9	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 15mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	2.6	—
Gate-Source Breakdown Voltage	VGSO	IGS= -50μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	4.5	6.5

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**ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	3.5
Total Power Dissipation (Tc= 25°C)	PT	W	23.1
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-11D1B)**

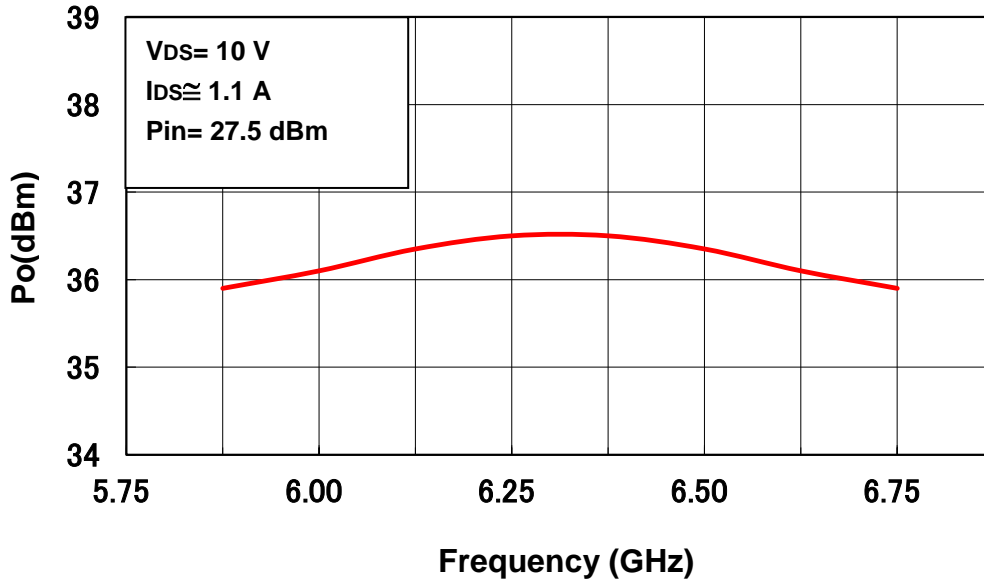


**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

**RF PERFORMANCE**

**Output Power vs. Frequency**



**Output Power vs. Input Power**

